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November 2013

# FQPF33N10L

# N-Channel QFET<sup>®</sup> MOSFET 100 V, 18 A, 52 m $\Omega$

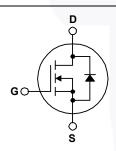
## **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 18 A, 100 V,  $R_{DS(on)}$  = 52 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 9 A
- Low Gate Charge (Typ. 30 nC)
- Low Crss (Typ. 70 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF33N10L	Unit	
$V_{DSS}$	Drain-Source Voltage		100	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	C)	18	Α	
	- Continuous (T <sub>C</sub> = 100	°C)	12.7	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	72	Α	
$V_{GSS}$	Gate-Source Voltage		± 20	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	430	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	18	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	4.1	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		41	W	
	- Derate above 25°C		0.27	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

# **Thermal Characteristics**

Symbol	Parameter	FQPF33N10L	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.7	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF33N10L	FQPF33N10L	TO-220F	Tube	N/A	N/A	50 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	ava ata viati a a					
BV <sub>DSS</sub>	aracteristics  Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C		0.09		V/°C
I <sub>DSS</sub>	7 0 1 1/1 1 1 1 1	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μА
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 9 \text{ A}$		0.039 0.043	0.052 0.055	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 9 A		22		S
	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1250	1630	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		305	400	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70	90	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 33 A,		17	45	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		470	950	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			70	150	ns
		(Note 4)		120	250	
t <sub>f</sub>	Turn-Off Fall Time					ns
t <sub>f</sub> Q <sub>g</sub>	Turn-Off Fall Time  Total Gate Charge	V <sub>DS</sub> = 80 V, I <sub>D</sub> = 33 A,		30	40	ns nC
		V <sub>DS</sub> = 80 V, I <sub>D</sub> = 33 A, V <sub>GS</sub> = 5 V		30 4.7	40	

# **Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current		 	18	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		 	72	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A	 	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 33 A,	 90		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs	 0.26		μС

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 2.0 mH,  $I_{AS}$  = 18 A,  $V_{DD}$  = 25 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 3.  $I_{SD}$   $\leq$  33 A, di/dt  $\leq$  300 A/µs,  $V_{DD}$   $\leq$  BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 4. Essentially Independent of Operating Temperature.

# **Typical Characteristics**

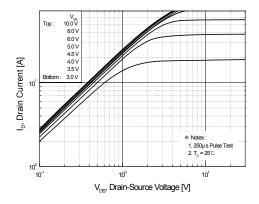
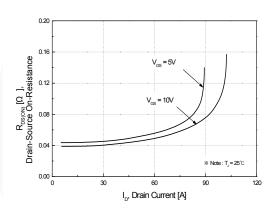


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



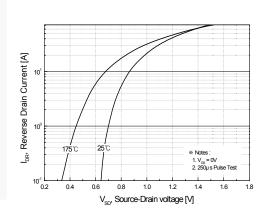
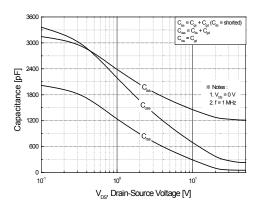


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



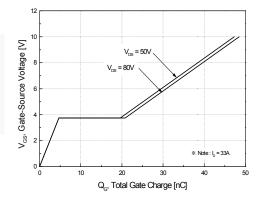


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)

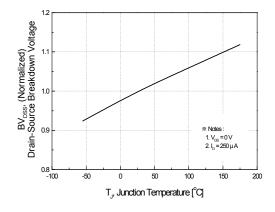
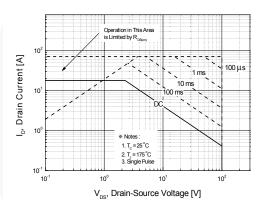


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



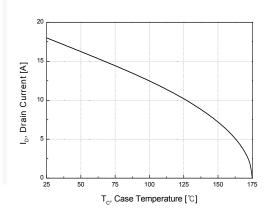


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

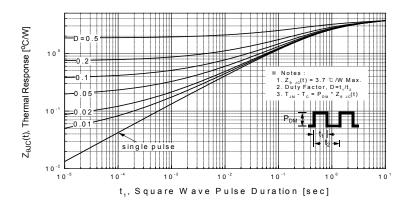


Figure 11. Transient Thermal Response Curve

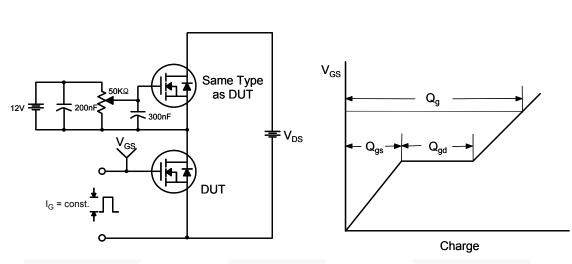


Figure 12. Gate Charge Test Circuit & Waveform

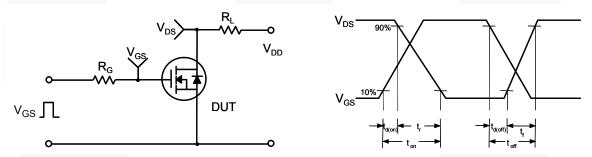


Figure 13. Resistive Switching Test Circuit & Waveforms

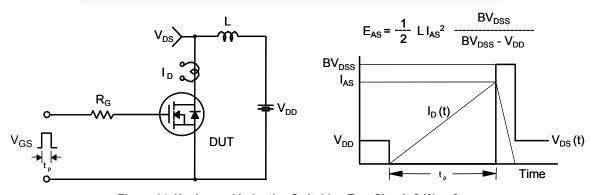
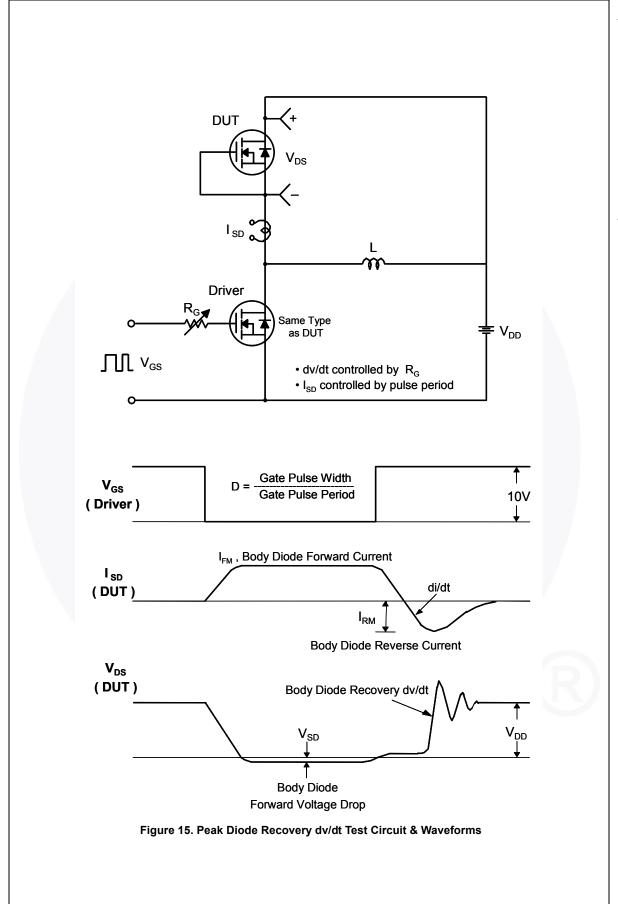


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

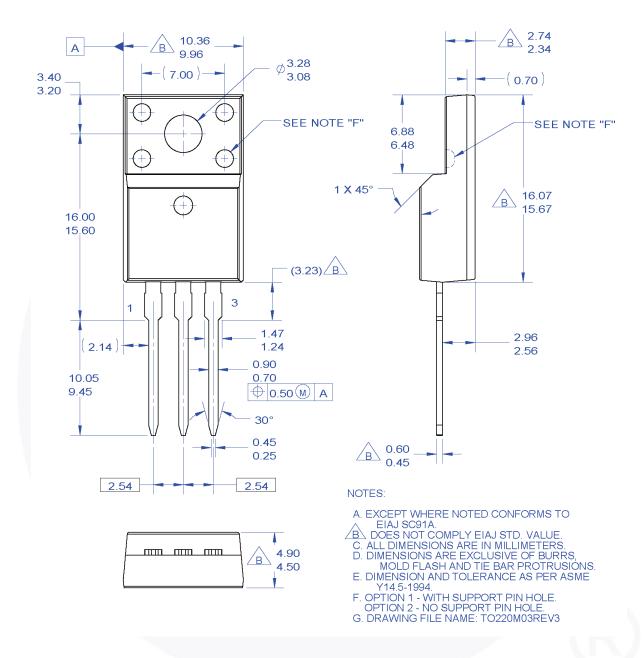


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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